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APPLICATION NO.	FILING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO
10/635,647	08/07/2003	Jun-hee Choi	030681-568	8798
21839	7590 03/12/2004		EXAMINER	
BURNS DOANE SWECKER & MATHIS L L P POST OFFICE BOX 1404			COLON, GERMAN	
	IA, VA 22313-1404		ART UNIT PAPER NUMBI	
	,		2879	

DATE MAILED: 03/12/2004

Please find below and/or attached an Office communication concerning this application or proceeding.

			AVC
	Application No.	Applicant(s)	
055 4 4 5	10/635,647	CHOI ET AL.	
Office Action Summary	Examiner	Art Unit	
	German Colón	2879	
The MAILING DATE of this communication Period for Reply	on appears on the cover sheet w	th the correspondence addr	ess
A SHORTENED STATUTORY PERIOD FOR ITHE MAILING DATE OF THIS COMMUNICAT - Extensions of time may be available under the provisions of 37 after SIX (6) MONTHS from the mailing date of this communicated if the period for reply specified above, is less than thirty (30) day if NO period for reply is specified above, the maximum statutory Failure to reply within the set or extended period for reply will, be Any reply received by the Office later than three months after the earned patent term adjustment. See 37 CFR 1.704(b).	TION. CFR 1.136(a). In no event, however, may a rition. s, a reply within the statutory minimum of thiriver priod will apply and will expire SIX (6) MON by statute, cause the application to become AB	reply be timely filed ty (30) days will be considered timely. ITHS from the mailing date of this comi BANDONED (35 U.S.C. § 133).	munication.
Status	•		
1) Responsive to communication(s) filed or	1 .		
,— ,	This action is non-final.		
3) Since this application is in condition for a closed in accordance with the practice up			nerits is
Disposition of Claims			
4) ⊠ Claim(s) 1 and 2 is/are pending in the ap 4a) Of the above claim(s) is/are w 5) □ Claim(s) is/are allowed. 6) ⊠ Claim(s) 1 and 2 is/are rejected. 7) □ Claim(s) is/are objected to. 8) □ Claim(s) are subject to restriction	ithdrawn from consideration.		
Application Papers			
9)⊠ The specification is objected to by the Ex	aminer.		
10) The drawing(s) filed on is/are: a)			
Applicant may not request that any objection			
Replacement drawing sheet(s) including the 11) The oath or declaration is objected to by	•		
Priority under 35 U.S.C. § 119			
12) Acknowledgment is made of a claim for for a) All b) Some * c) None of: 1. Certified copies of the priority docu 2. Certified copies of the priority docu 3. Copies of the certified copies of the application from the International E * See the attached detailed Office action for	uments have been received. uments have been received in A e priority documents have been Bureau (PCT Rule 17.2(a)).	application No. <u>09/754,275</u> . received in this National St	tage
Attachment(s)			
1) Notice of References Cited (PTO-892)		Summary (PTO-413) s)/Mail Date	
 Notice of Draftsperson's Patent Drawing Review (PTO-93) Information Disclosure Statement(s) (PTO-1449 or PTO-Paper No(s)/Mail Date <u>080703</u>. 		nformal Patent Application (PTO-1	52)

DETAILED ACTION

Specification

1. The disclosure is objected to because of the following informalities:

Page 5, line 1, refers to a gate electrode 160; however, on line 4, reference number 140 identifies said gate electrode.

Page 6, line 3, refers to a focus gate electrode 190; however, on line 4, reference number 191 identifies said focus gate electrode.

Appropriate correction is required.

Claim Rejections - 35 USC § 102

2. The following is a quotation of the appropriate paragraphs of 35 U.S.C. 102 that form the basis for the rejections under this section made in this Office action:

A person shall be entitled to a patent unless -

- (b) the invention was patented or described in a printed publication in this or a foreign country or in public use or on sale in this country, more than one year prior to the date of application for patent in the United States.
- 3. Claims 1 and 2 are rejected under 35 U.S.C. 102(b) as being anticipated by Choo (US 5,910,704).

Regarding claim 1, Choo discloses a field emission device comprising:

a substrate 10;

a cathode 11 formed over the substrate;

micro-tips 15 having nano-sized surface features, formed on the cathode;

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a gate insulating layer 13A with wells 131A each of which a single micro-tip is located in, the gate insulating layer formed over the substrate;

a gate electrode 14A with gates 141A aligned with the wells such that each of the microtips is exposed through a corresponding gate, the gate electrode formed on the gate insulating layer;

a focus gate insulation layer 13B having openings each of which one or more gates correspond to, the focus gate insulation layer formed on the gate electrode; and

a focus gate electrode 14B with focus gates aligned with the openings of the focus gate insulation layer, the focus gate electrode formed on the focus gate insulation layer.

Referring to claim 2. Choo discloses a resistor layer 12 formed over the cathode.

Claim 1 is rejected under 35 U.S.C. 102(b) as being anticipated by Yamaguchi et al. (US 4. 5,955,850).

Regarding claim 1. Yamaguchi discloses a field emission device comprising (see at least Fig. 3):

a substrate 1;

a cathode 2 formed over the substrate;

micro-tips 5 having nano-sized surface features, formed on the cathode;

a gate insulating layer 3 with wells each of which a single micro-tip is located in, the gate insulating layer formed over the substrate;

a gate electrode 4 with gates aligned with the wells such that each of the micro-tips is exposed through a corresponding gate, the gate electrode formed on the gate insulating layer;

a focus gate insulation layer 3' having openings each of which one or more gates

correspond to, the focus gate insulation layer formed on the gate electrode; and

a focus gate electrode 7 with focus gates aligned with the openings of the focus gate

insulation layer, the focus gate electrode formed on the focus gate insulation layer.

Prior Art of Record

The prior art made of record and not relied upon is considered pertinent to applicant's

disclosure:

Okamoto (US 5,850,120) discloses a field emission device which reads on at least claim

1.

Contact Information

Any inquiry concerning this communication or earlier communications from the

examiner should be directed to German Colón whose telephone number is 571-272-2451. The

examiner can normally be reached on Monday thru Thursday, from 8:30 to 6:00.

If attempts to reach the examiner by telephone are unsuccessful, the examiner's

supervisor, Nimesh Patel can be reached on 571-272-2457. The fax phone number for the

organization where this application or proceeding is assigned is 703-872-9306.

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Information regarding the status of an application may be obtained from the Patent Application Information Retrieval (PAIR) system. Status information for published applications may be obtained from either Private PAIR or Public PAIR. Status information for unpublished applications is available through Private PAIR only. For more information about the PAIR system, see http://pair-direct.uspto.gov. Should you have questions on access to the Private PAIR system, contact the Electronic Business Center (EBC) at 866-217-9197 (toll-free).

gc

ASHOK PATEL
PRIMARY EXAMINER